

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Lukanc et al.  
Title: METHOD OF ENHANCING GATE  
PATTERNING PROPERTIES  
WITH REFLECTIVE HARD MASK  
Appl. No.: 09/845,654  
Filing Date: 04/30/2001  
Examiner: Maldonado, Julio J.  
Art Unit: 2823



**CERTIFICATE OF MAILING**  
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Jeanne Johnson  
(Printed Name)

*Jeanne Johnson*  
(Signature)

July 3, 2002  
(Date of Deposit)

#4/Amend  
A  
7/24/02  
VJ

AMENDMENT

Commissioner for Patents  
Box NON-FEE AMENDMENT  
Washington, D.C. 20231

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Sir:

This communication is responsive to the Office Action dated April 10, 2002, concerning the above-referenced patent application.

Please amend the application as follows:

**In the Specification:**

Please replace paragraph numbers [0001], [0004], and [0032] with the following paragraphs pursuant to 37 C.F.R. § 1.121. The changes are shown explicitly in the attached "Version with Markings to Show Changes Made"

a' [0001] This application is related to U.S. patent Application No. 09/845,656, Attorney Docket No. 39153/366 (F0807), entitled USE OF SILICON CONTAINING IMAGING LAYER TO DEFINE SUB-RESOLUTION GATE STRUCTURES, and U.S. Patent Application No. 09/845,649, Attorney Docket No. 39153/367 (F0808), entitled BI-LAYER TRIM ETCH PROCESS TO FORM INTEGRATED CIRCUIT GATE STRUCTURES, both of which are assigned to the same assignee as this application and are filed on an even day herewith.